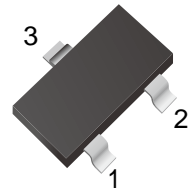
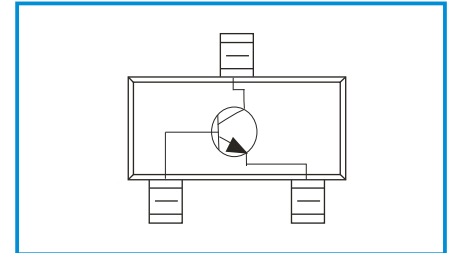


Transistor(NPN)

Features

- Low equivalent on-resistance
- Marking: 491

1. BASE
2. EMITTER
3. COLLECTOR


Functional Diagram


Maximum Ratings($T_a=25$ unless otherwise noted)

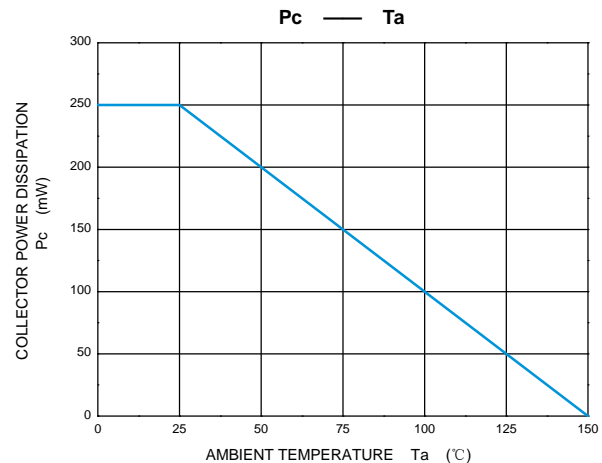
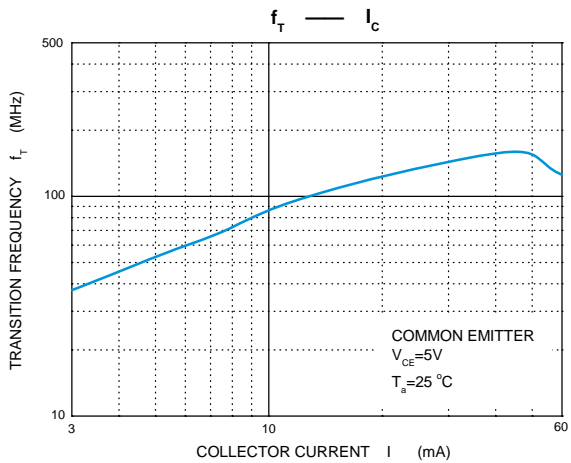
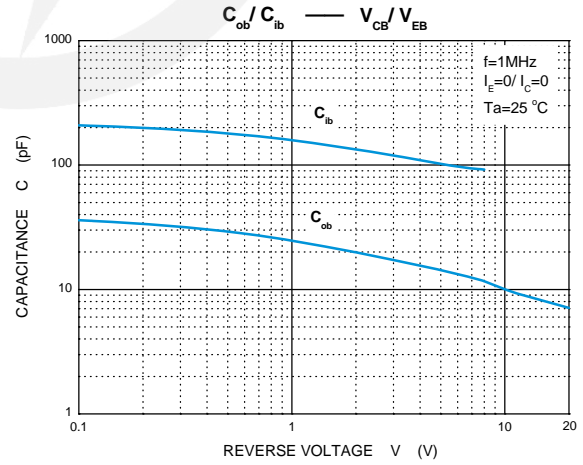
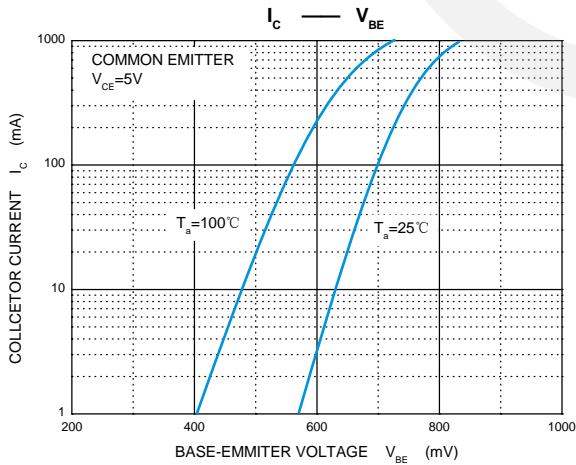
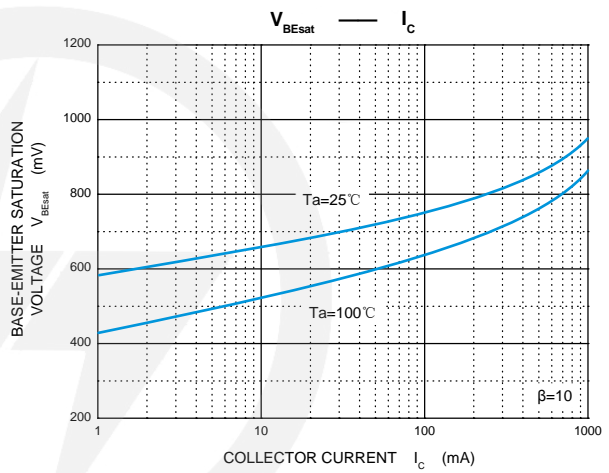
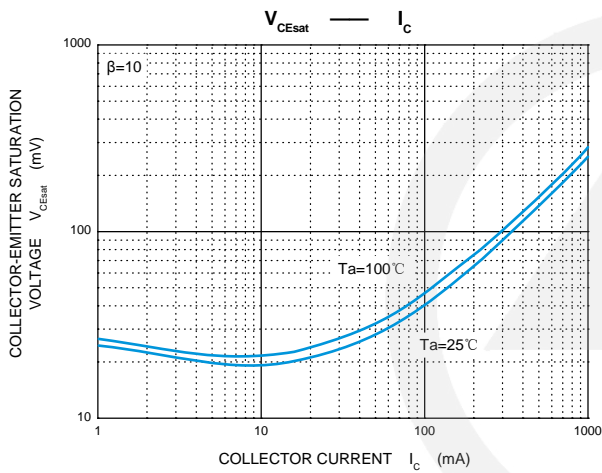
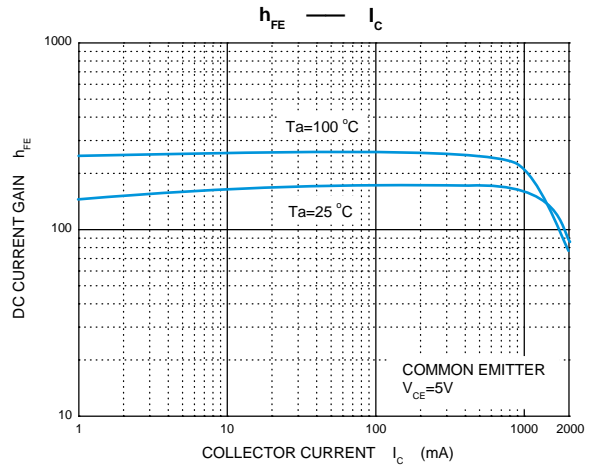
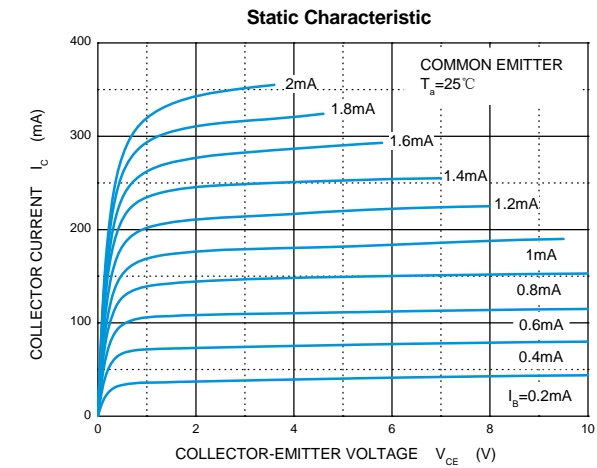
Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	80	V
V_{CE0}	Collector-Emitter Voltage	60	V
V_{EB0}	Emitter-Base Voltage	5	V
I_C	Collector Current	1	A
I_{CM}	Peak Pulse Current	2	A
P_C	Collector Power Dissipation	250	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	500	$^{\circ}C/W$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}C$

Electrical characteristics ($T_a=25$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C=100\mu A, I_E=0$	80			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}^1$	$I_C=10mA, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EB0}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CB0}	$V_{CB}=60V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB}=4V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=5V, I_C=1mA$	100			
	$h_{FE(2)}^1$	$V_{CE}=5V, I_C=500mA$	100		300	
	$h_{FE(3)}^1$	$V_{CE}=5V, I_C=1A$	80			
	$h_{FE(4)}^1$	$V_{CE}=5V, I_C=2A$	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}^1$	$I_C=500mA, I_B=50mA$			0.25	V
	$V_{CE(sat)2}^1$	$I_C=1A, I_B=100mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}^1$	$I_C=1A, I_B=100mA$			1.1	V
Base-emitter voltage	V_{BE}^1	$V_{CE}=5V, I_C=1A$			1	V
Transition frequency	f_T	$V_{CE}=10V, I_C=50mA, f=100MHz$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$			10	pF

¹Measured under pulsed conditions, Pulse width=300 μs , Duty cycle $\leq 2\%$.

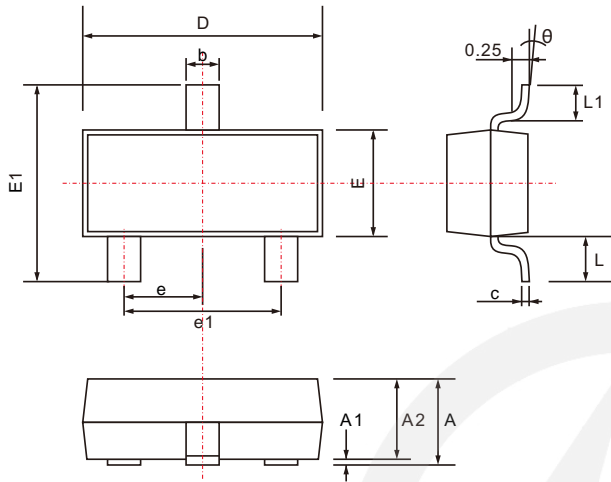
Typical Characteristics



SOT-23 Package Outline

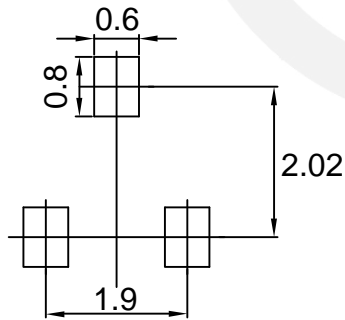
Plastic surface mounted package

Unit: mm



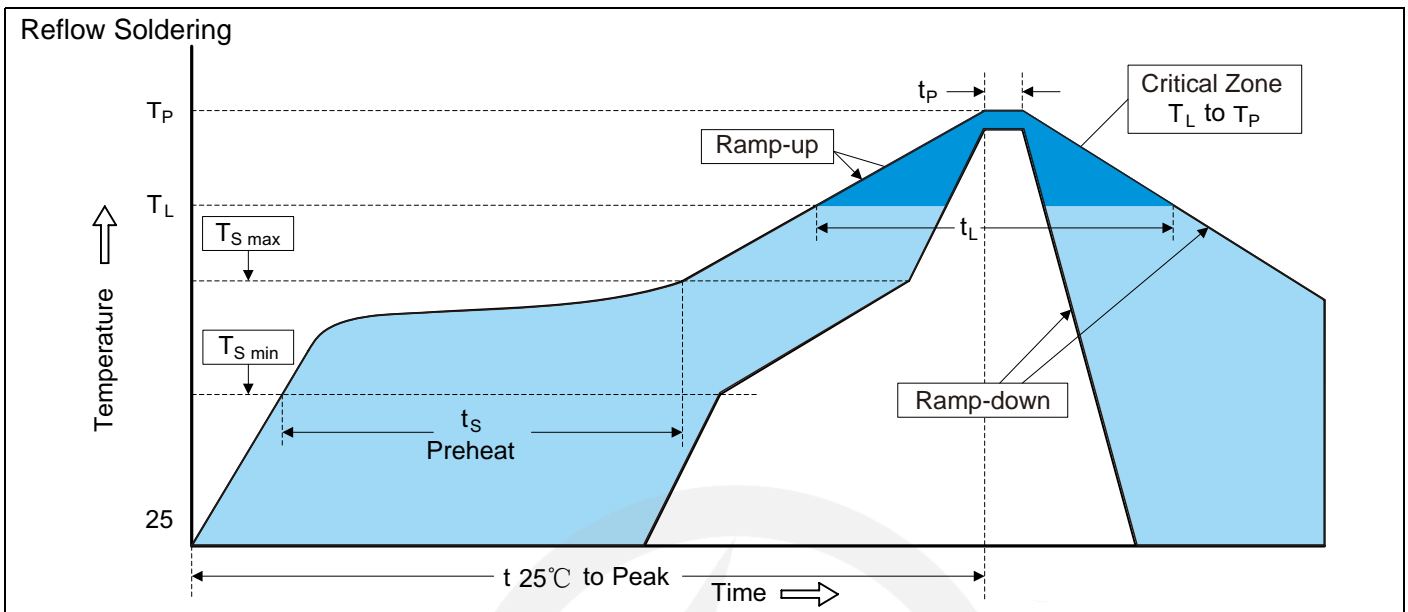
SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	0.900	1.200
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.200
D	2.700	3.100
E	1.200	1.400
E1	2.200	3.000
e	0.950 TYP.	
e1	1.750	2.050
L	0.550 TYP.	
L1	0.300	0.500
θ	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm
3. The pad layout is for reference purpose only.

Recommended Soldering Conditions

Recommended Conditions

Profile Feature	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.
Preheat -Temperature Min ($T_{S\ min}$) -Temperature Max ($T_{S\ max}$) -Time (min to max) (t_s)	150°C 200°C 60-180 seconds
$T_{S\ max}$ to T_L -Ramp-up Rate	3°C/second max.
Time maintained above: -Temperature (T_L) -Time (t_L)	217°C 60-150 seconds
Peak Temperature (T_P)	260°C
Time within 5°C of actual Peak Temperature (t_P)	20-40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

7" Reel


D2	$\Phi 178.0 \pm 2.0$
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D3	$\Phi 50.0 \text{ Min.}$
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D4	$\Phi 13.0 \pm 0.5$
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W1	16.0 ± 2.0
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Quantity: 3000PCS